

CNX82A  
CNX82AX



**NON-BASE LEAD  
OPTICALLY COUPLED ISOLATOR  
PHOTOTRANSISTOR OUTPUT**

**APPROVALS**

- UL recognised, File No. E91231  
Package System " GG "

**'X' SPECIFICATION APPROVALS**

- VDE 0884 in 3 available lead form :-  
- STD  
- G form  
- SMD approved to CECC 00802
- Certified to EN60950 by :-  
Nemko - Certificate No. P01102464

**DESCRIPTION**

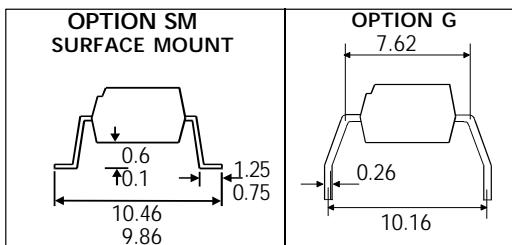
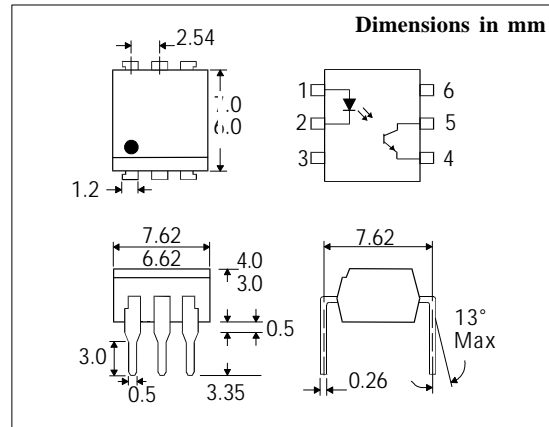
The CNX82A series of optically coupled isolator consists of an infrared light emitting diode and an NPN silicon photo transistor in a standard 6 pin dual in line plastic package with the base pin unconnected.

**FEATURES**

- High Current Transfer Ratio (40% min)
- Low Saturation Voltage suitable for TTL integrated circuits
- High  $BV_{CEO}$  (50V min)
- High Isolation Voltage ( $5.3kV_{RMS}, 7.5kV_{PK}$ )
- Base pin unconnected for improved noise immunity in high EMI environment

**APPLICATIONS**

- DC motor controllers
- Industrial systems controllers
- Signal transmission between systems of different potentials and impedances



**ABSOLUTE MAXIMUM RATINGS  
(25°C unless otherwise specified)**

Storage Temperature \_\_\_\_\_ -55°C to +150°C  
Operating Temperature \_\_\_\_\_ -55°C to +100°C  
Lead Soldering Temperature  
(1/16 inch (1.6mm) from case for 10 secs) 260°C

**INPUT DIODE**

Forward Current \_\_\_\_\_ 60mA  
Reverse Voltage \_\_\_\_\_ 6V  
Power Dissipation \_\_\_\_\_ 105mW

**OUTPUT TRANSISTOR**

Collector-emitter Voltage  $BV_{CEO}$  \_\_\_\_\_ 50V  
Emitter-collector Voltage  $BV_{ECO}$  \_\_\_\_\_ 6V  
Collector Current \_\_\_\_\_ 50mA  
Power Dissipation \_\_\_\_\_ 160mW

**POWER DISSIPATION**

Total Power Dissipation \_\_\_\_\_ 200mW  
(derate linearly 2.67mW/°C above 25°C)

**ISOCOM COMPONENTS LTD**  
Unit 25B, Park View Road West,  
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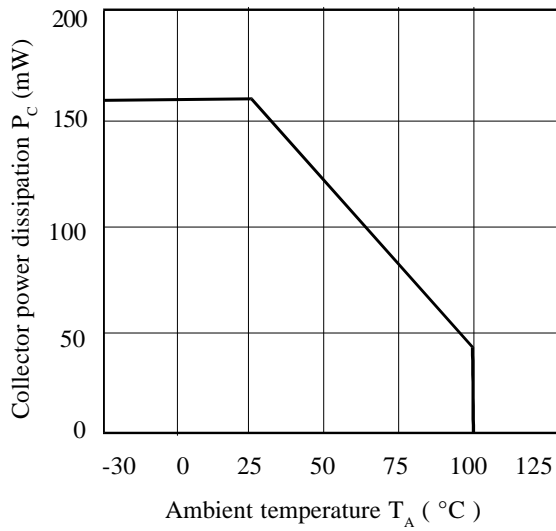
**ELECTRICAL CHARACTERISTICS (  $T_A = 25^\circ\text{C}$  Unless otherwise noted )**

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage ( $V_F$ )		1.2	1.5	V	$I_F = 10\text{mA}$
	Reverse Current ( $I_R$ )			10	$\mu\text{A}$	$V_R = 6\text{V}$
Output	Collector-emitter Breakdown ( $BV_{CEO}$ ) ( Note 2 )	50			V	$I_C = 1\text{mA}$
	Emitter-collector Breakdown ( $BV_{ECO}$ )	6			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current ( $I_{CEO}$ )			50	nA	$V_{CE} = 10\text{V}$
Coupled	Current Transfer Ratio ( $I_C / I_F$ ) (Note 2)	0.4	1.5			$10\text{mA } I_F, 0.4\text{V } V_{CE}$ $10\text{mA } I_F, 5\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.4	V	$10\text{mA } I_F, 4\text{mA } I_C$
	Input to Output Isolation Voltage $V_{ISO}$	5300 7500			$V_{RMS}$ $V_{PK}$	See note 1 See note 1
	Input-output Isolation Resistance $R_{ISO}$	$5 \times 10^{10}$			$\Omega$	$V_{IO} = 500\text{V}$ (note 1)
	Response Time - Rise, tr Response Time - Fall, tf		2 2		$\mu\text{s}$ $\mu\text{s}$	$V_{CC} = 5\text{V}, I_F = 10\text{mA},$ $R_L = 75\Omega$

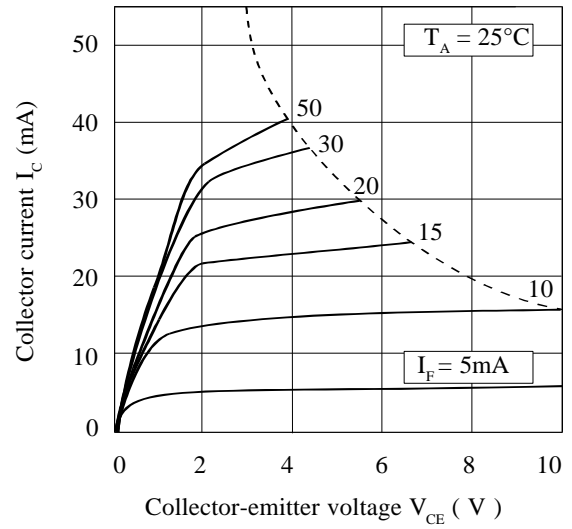
Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

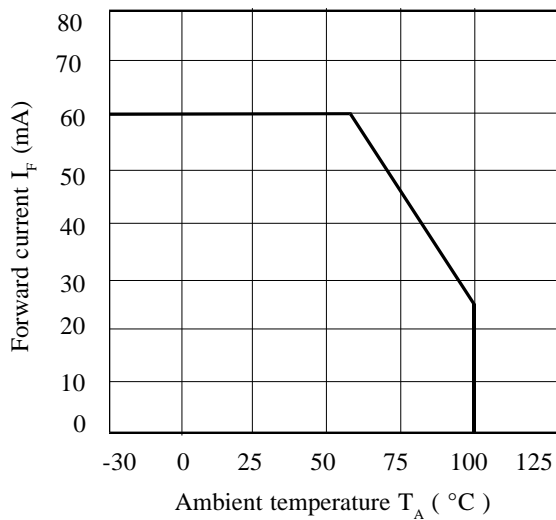
**Collector Power Dissipation vs. Ambient Temperature**



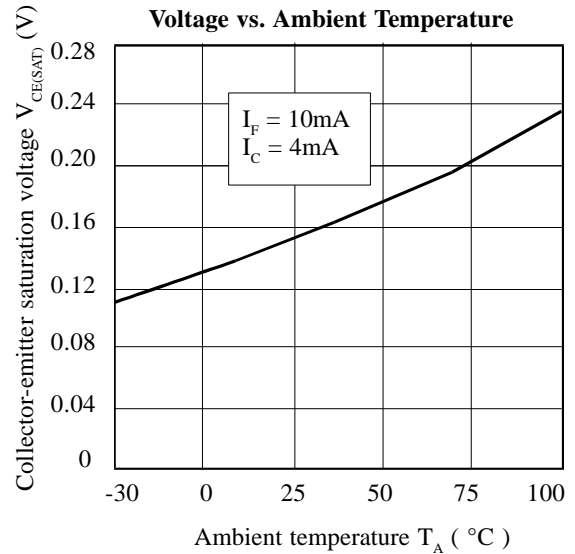
**Collector Current vs. Collector-emitter Voltage**



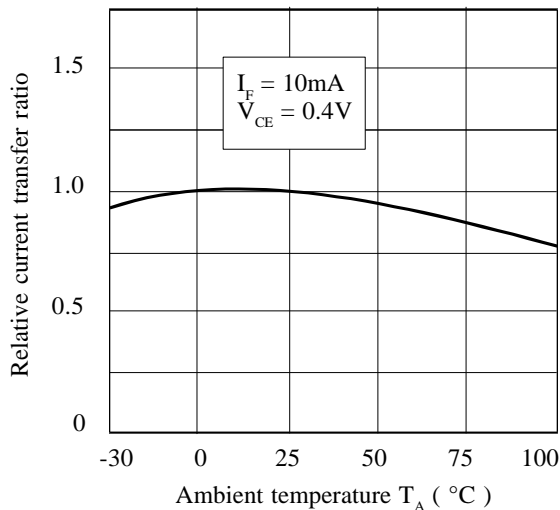
**Forward Current vs. Ambient Temperature**



**Collector-emitter Saturation Voltage vs. Ambient Temperature**



**Relative Current Transfer Ratio vs. Ambient Temperature**



**Relative Current Transfer Ratio vs. Forward Current**

